

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1561	"SnAgCu" or (Sn adj Ag adj Cu)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/15 07:48
L2	1121	"SnAgCu" or (Sn adj Ag adj Cu) near9 solder	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/15 07:48
L3	486	"SnAgCu" or (Sn adj Ag adj Cu) near9 solder with (substrate or wafer or carrier or base or plate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/15 07:50
L4	376	"SnAgCu" or (Sn adj Ag adj Cu) near9 solder with (substrate or wafer or carrier or base or plate) and seal\$4 and resin and (curing or cure) and temperature	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/15 07:52
L5	358	"SnAgCu" or (Sn adj Ag adj Cu) near9 solder with (substrate or wafer or carrier or base or plate) and seal\$4 and resin and (curing or cure) and temperature and (device or circuit) with inspect\$4	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/15 07:54
L6	358	"SnAgCu" or (Sn adj Ag adj Cu) near9 solder with (substrate or wafer or carrier or base or plate) and seal\$4 and resin and (curing or cure) and temperature and (device or circuit) with inspect\$4 and (baking or bake)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/15 07:54

L7	358	"SnAgCu" or (Sn adj Ag adj Cu) near9 solder with (substrate or wafer or carrier or base or plate) and seal\$4 and resin and (curing or cure) and (first near temperature) and (device or circuit) with inspect\$4 and (baking or bake)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/15 07:56
L8	358	"SnAgCu" or (Sn adj Ag adj Cu) near9 solder with (substrate or wafer or carrier or base or plate) and seal\$4 and resin and (curing or cure) and (first near temperature) and (device or circuit) with inspect\$4 and (baking or bake) and (second near temperature)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/15 07:56
L9	358	"SnAgCu" or (Sn adj Ag adj Cu) near9 solder with (substrate or wafer or carrier or base or plate) and seal\$4 and resin and (curing or cure) and (first near temperature) and (device or circuit) with inspect\$4 and (baking or bake) and (second near temperature) and potting	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/15 07:57
L10	358	"SnAgCu" or (Sn adj Ag adj Cu) near9 solder with (substrate or wafer or carrier or base or plate) and seal\$4 and (thermoset\$4 near9 resin) and (curing or cure) and (first near temperature) and (device or circuit) with inspect\$4 and (baking or bake) and (second near temperature) and potting	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/15 08:00

L11	149787	"SnAgCu" or (Sn adj Ag adj Cu) near9 solder with (substrate or wafer or carrier or base or plate) and seal\$4 and (thermoset\$4 near9 resin) and (curing or cure) and (first near temperature) and (device or circuit) with inspect\$4 and (baking or bake) and (second near temperature) and potting (resin or epoxy) near9 seal\$4	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/15 08:09
L12	358	"SnAgCu" or (Sn adj Ag adj Cu) near9 solder with (substrate or wafer or carrier or base or plate) and seal\$4 and (thermoset\$4 near9 resin) and (curing or cure) and (first near temperature) and (device or circuit) with inspect\$4 and (baking or bake) and (second near temperature) and potting and (resin or epoxy) near9 (seal\$4 or encapsulat\$4)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/15 08:11
L13	0	("SnAgCu" or (Sn adj Ag adj Cu) near9 solder with (substrate or wafer or carrier or base or plate)) and (resin or epoxy) and (curing or cure) and (first near temperature) and ((device or circuit) with inspect\$4) and (baking or bake) and (second near temperature) and potting and (resin or epoxy) near9 (seal\$4 or encapsulat\$4)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/15 08:59
L14	117	("SnAgCu" or (Sn adj Ag adj Cu) near9 solder with (substrate or wafer or carrier or base or plate)) and (resin or epoxy) and (curing or cure)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/15 09:04

L15	8	("SnAgCu" or (Sn adj Ag adj Cu) near9 solder with (substrate or wafer or carrier or base or plate)) and (resin or epoxy) and (curing or cure) and (first near temperature) and (second near temperature)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/15 09:05
L16	0	("SnAgCu" or (Sn adj Ag adj Cu) near9 solder with (substrate or wafer or carrier or base or plate)) and (resin or epoxy) and (curing or cure) and (first near temperature) and (second near temperature) and (baking or bake) and inspect\$4	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/15 09:05
L17	0	("SnAgCu" or (Sn adj Ag adj Cu) near9 solder with (substrate or wafer or carrier or base or plate)) and (resin or epoxy) and (curing or cure) and (first near temperature) and (second near temperature) and (baking or bake)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/15 09:06
L18	7	("SnAgCu" or (Sn adj Ag adj Cu) near9 solder with (substrate or wafer or carrier or base or plate)) and (resin or epoxy) and (curing or cure) and (baking or bake)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/15 09:10
L19	7	("SnAgCu" or (Sn adj Ag adj Cu) near9 solder with (substrate or wafer or carrier or base or plate)) and (curing or cure) and (baking or bake)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/15 09:16

L20	0	(curing or cure) and (baking or bake) and (seal\$4 or encapsula\$6) with (device or circuit) and (resin or epoxy) and (first near temperature) and (second near temperature) and inspect\$4 with (circuit or device)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/15 09:18
L21	35	(curing or cure) and (baking or bake) and (seal\$4 or encapsula\$6) with (device or circuit) and (resin or epoxy) and (first near temperature) and (second near temperature)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/15 09:19
L22	5032	(first adj temperature) and (second adj temperature) and (third adj temperature)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/15 09:38
L23	116	(first adj temperature) and (second adj temperature) and (third adj temperature) and (cure or curing) with (epoxy or resin)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/15 09:38
L24	67	(first adj temperature) and (second adj temperature) and (third adj temperature) and (cure or curing) with (epoxy or resin) and (bake or baking or heat \$4) with (resin or epoxy)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/15 09:39
L25	39	(first adj temperature) and (second adj temperature) and (third adj temperature) and (cure or curing) with (epoxy or resin) and (bake or baking or heat \$4) with (resin or epoxy) and (circuit or device)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/15 09:39

L26	1	(first adj temperature) and (second adj temperature) and (third adj temperature) and (cure or curing) with (epoxy or resin) and (bake or baking or heat \$4) with (resin or epoxy) and (inspect\$4 with (circuit or device))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/15 09:40
L27	0	(first adj temperature) and (second adj temperature) and (third adj temperature) and (cure or curing) with (epoxy or resin) and (bake or baking or heat \$4) with (resin or epoxy) and "SnAgCu"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/15 09:40
L28	0	(first adj temperature) and (second adj temperature) and (third adj temperature) and (cure or curing) with (epoxy or resin) and (bake or baking or heat \$4) with (resin or epoxy) and (Sn adj Ag adj Cu)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/15 09:41
L29	136454	inspect\$4 with (circuit or device)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/15 09:41
L30	46	inspect\$4 with (circuit or device) and ("SnAgCu" or (Sn adj Ag adj Cu))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/15 09:42
L31	42	inspect\$4 with (circuit or device) and ("SnAgCu" or (Sn adj Ag adj Cu)) and (substrate or wafer or carrier or base or plate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/15 09:42

L32	5	inspect\$4 with (circuit or device) and ("SnAgCu" or (Sn adj Ag adj Cu)) and (substrate or wafer or carrier or base or plate) and potting	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/15 09:43
L33	5	inspect\$4 with (circuit or device) and ("SnAgCu" or (Sn adj Ag adj Cu)) and (substrate or wafer or carrier or base or plate) and potting and mold\$4	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/15 09:43
L34	3	("SnAgCu" or (Sn adj Ag adj Cu)) and (third adj temperature)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/15 09:50
S1	15637	resin near4 (bak\$4 or heat\$4 or anneal\$4) and cur\$4 and (temp\$4 or therm\$4) and (semiconductor or wafer or substrate)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2006/06/29 14:35
S2	1967	resin near4 (bak\$4 or heat\$4 or anneal\$4) and cur\$4 and (temp\$4 or therm\$4) and (semiconductor or wafer or substrate) and thermoset	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/08/31 08:21
S3	586	resin near4 (bak\$4 or heat\$4 or anneal\$4) and cur\$4 and (temp\$4 or therm\$4) and (semiconductor or wafer or substrate) and thermoset and circuit	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/08/31 08:22
S4	341	resin near4 (bak\$4 or heat\$4 or anneal\$4) and cur\$4 and (temp\$4 or therm\$4) and (semiconductor or wafer or substrate) and thermoset and circuit and mold\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/08/31 08:22

S5	109	resin near4 (bak\$4 or heat\$4 or anneal\$4) and cur\$4 and (temp\$4 or therm\$4) and (semiconductor or wafer or substrate) and thermoset and circuit and mold\$4 and pot\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/08/31 08:22
S6	69	resin near4 (bak\$4 or heat\$4 or anneal\$4) and cur\$4 and (temp\$4 or therm\$4) and (semiconductor or wafer or substrate) and thermoset and circuit and mold\$4 and pot\$4 and seal\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/08/31 08:22
S7	53	resin near4 (bak\$4 or heat\$4 or anneal\$4) and cur\$4 and (temp\$4 or therm\$4) and (semiconductor or wafer or substrate) and thermoset and circuit and mold\$4 and pot\$4 and seal\$4 and lead	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/08/31 08:23
S8	43	resin near4 (bak\$4 or heat\$4 or anneal\$4) and cur\$4 and (temp\$4 or therm\$4) and (semiconductor or wafer or substrate) and thermoset and circuit and mold\$4 and pot\$4 and seal\$4 and lead and electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/08/31 08:23
S9	41	resin near4 (bak\$4 or heat\$4 or anneal\$4) and cur\$4 and (temp\$4 or therm\$4) and (semiconductor or wafer or substrate) and thermoset and circuit and mold\$4 and pot\$4 and seal\$4 and lead and electrode and solder	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/08/31 08:24

S10	0	resin near4 (bak\$4 or heat\$4 or anneal\$4) and cur\$4 and (temp\$4 or therm\$4) and (semiconductor or wafer or substrate) and thermoset and circuit and mold\$4 and pot\$4 and seal\$4 and lead and electrode and solder and (438/585. ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/08/31 08:23
S11	4204	(semiconductor or substrate or wafer) and (thermoset\$4 near4 resin) and cur\$3 and bak\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/29 14:42
S12	33	(semiconductor or substrate or wafer) and (thermoset\$4 near4 resin) and cur\$3 and bak\$3 and seal\$3 and mold\$3 and pot\$3 and lead and temperature and chip	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/29 14:45
S13	21	(semiconductor or substrate or wafer) and (thermoset\$4 near4 resin) and cur\$3 and bak\$3 and seal\$3 and mold\$3 and pot\$3 and lead and temperature and (semiconductor near4 chip) and solder	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/29 14:46
S14	38625	(semiconductor or substrate or wafer) and (thermoset\$4 near4 resin)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/15 11:52
S15	11389	(semiconductor or substrate or wafer) and (thermoset\$4 near4 resin) and (curing near9 resin)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/15 11:53
S16	107	(semiconductor or substrate or wafer) and (bak\$4 near9 (thermoset\$4 near4 resin)) and (curing near9 resin)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/15 11:54

S17	79	(semiconductor or substrate or wafer) and (bak\$4 near9 (thermoset \$4 near4 resin)) and (curing near9 resin) and temperature	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/15 11:54
S18	2	(semiconductor or substrate or wafer) and (bak\$4 near9 (thermoset \$4 near4 resin)) and (curing near9 resin) and temperature and mold \$4 and pot\$4 and (aging near4 test\$4)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/15 12:05
S19	0	(semiconductor or substrate or wafer) and (bak\$4 near9 (thermoset \$4 near4 resin)) and (curing near9 resin) and temperature and mold \$4 and pot\$4 and (reliab \$4 near4 test\$4)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/15 12:05
S20	0	(semiconductor or substrate or wafer) and (bak\$4 near9 (thermoset \$4 near4 resin)) and (curing near9 resin) and temperature and mold \$4 and pot\$4 and inspect	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/15 12:06
S21	6	(semiconductor or substrate or wafer) and (bak\$4 near9 (thermoset \$4 near4 resin)) and (curing near9 resin) and temperature and mold \$4 and pot\$4 and test	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/15 12:16
S22	1	seal near9 (semiconductor or substrate or wafer) and (bak\$4 near9 (thermoset \$4 near4 resin)) and (curing near9 resin) and temperature and mold \$4 and pot\$4	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/15 12:17
S23	16	seal near9 (semiconductor or substrate or wafer) and (bak\$4 near9 resin) and (curing near9 resin) and temperature and mold \$4 and pot\$4	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/15 12:21

S25	81	(seal or enclose) near9 (semicondcutor or substrate or wafer) and (curing near9 resin) and (bak\$4 near9 resin) and temperature	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/29 08:31
S26	14	(seal or enclose) near9 (semicondcutor or substrate or wafer) and (curing near9 resin) and (bak\$4 near9 resin) and temperature and (transfer near4 mold) and (mount\$4 near9 (semicondcutor or substrate or wafer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/29 10:32
S27	17	seal near9 (semiconductor or circuit or device) and (bak\$4 near9 resin) and (curing near9 resin) and temperature and mold \$4 and pot\$4	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/22 09:51
S28	273	(resin near9 device) and ((curing or cure) near9 resin) and (bak\$4 near9 (temperature or heat)) and (semiconductor or wafer or substrate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/22 10:02
S29	3	(resin near9 device) and ((curing or cure) near9 resin) and (bak\$4 near9 (temperature or heat)) and (semiconductor or wafer or substrate) and (inspect near9 device)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/22 10:23
S30	0	(resin near9 device) and ((curing or cure) near9 resin) and (bak\$4 near9 (temperature or heat)) and (semiconductor or wafer or substrate) and (inspect near9 device) and ((mount or holder) near9 (device or circuit))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/22 10:04

S31	1	(resin near9 device) and ((curing or cure) near9 resin) and (bak\$4 near9 (temperature or heat)) and (semiconductor or wafer or substrate) and (inspect near9 device) and seal	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/22 10:24
S32	55	(seal\$4 near9 (resin near9 device)) and ((curing or cure) near9 resin) and (bak\$4 near9 (temperature or heat)) and (semiconductor or wafer or substrate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/03 10:46
S33	1260	(cure or curing) near9 "thermoset resin"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/03 10:47
S34	220	(cure or curing) near9 "thermoset resin" near9 temperature	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/03 11:04
S35	1	(cure or curing) near9 "thermoset resin" near9 temperature and (bak\$4 near9 "thermoset resin")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/03 11:31
S36	4	(cure or curing) near9 "thermoset resin" near9 temperature and (bak\$4 near9 resin)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/03 11:42
S37	80	(cure or curing) near9 "thermoset resin" near9 temperature and (semiconductor or substrate or wafer)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/03 11:43
S38	1	(cure or curing) near9 "thermoset resin" near9 temperature and (semiconductor or substrate or wafer) and (bak\$4 near9 resin)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/03 11:45

S39	1	(cure or curing) near9 ("thermoset resin" or eopxy) near9 temperature and (semiconductor or substrate or wafer) and (bak\$4 near9 resin)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/03 11:46
S40	1	(cure or curing) near9 ("thermoset resin" or eopxy) near9 temperature and (semiconductor or substrate or wafer) and (bak\$4 near9 (resin or epoxy))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/03 11:46
S41	186	seal\$4 near9 (semiconductor or substrate or wafer) and ((resin or epoxy) near9 (semiconductor or substrate or wafer)) and ((cure or curing) near9 (resin or epoxy)) and ((bake or baking) near9 (epoxy or resin)) and temperature	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/08 08:54
S42	21	seal\$4 near9 (semiconductor or substrate or wafer) and ((resin or epoxy) near9 (semiconductor or substrate or wafer)) and ((cure or curing) near9 (resin or epoxy)) and ((bake or baking) near9 (epoxy or resin)) and temperature and (thermal near9 (cure or curing))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/08 10:01
S43	19669	(transfer near4 mold)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/08 10:01
S44	154768	(chip or IC or device or semiconductor) near9 resin	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/19 07:49

S45	19415	(chip or IC or device or semiconductor) near9 resin and ((cure or curing) near9 resin)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/19 07:50
S46	377	(chip or IC or device or semiconductor) near9 resin and ((cure or curing) near9 resin) and ((bake or baking) near9 resin)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/19 07:51
S47	52	(chip or IC or device or semiconductor) near9 resin and ((cure or curing) near9 resin) and ((bake or baking) near9 resin) and (first near9 temperature)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/19 07:51
S48	32	(chip or IC or device or semiconductor) near9 resin and ((cure or curing) near9 resin) and ((bake or baking) near9 resin) and (first near9 temperature) and (second near9 temperature)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/19 07:51
S49	0	(chip or IC or device or semiconductor) near9 resin and ((cure or curing) near9 resin) and ((bake or baking) near9 resin) and (first near9 temperature) and (second near9 temperature) and (third near9 temperature)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/19 07:52
S50	0	(chip or IC or device or semiconductor) near9 resin and ((cure or curing) near9 resin) and ((bake or baking) near9 resin) and (first near9 temperature) and (second near9 temperature) and (trnsfer near mold\$4)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/19 07:53

S51	0	(chip or IC or device or semiconductor) near9 resin and ((cure or curing) near9 resin) and ((bake or baking) near9 resin) and (first near9 temperature) and (second near9 temperature) and (transfer near mold\$4)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/19 07:54
S52	0	(chip or IC or device or semiconductor) near9 resin and ((cure or curing) near9 resin) and ((bake or baking) near9 resin) and (first near9 temperature) and (second near9 temperature) and (transfer near9 mold\$4)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/19 07:54
S53	9	(chip or IC or device or semiconductor) near9 resin and ((cure or curing) near9 resin) and ((bake or baking) near9 resin) and (first near9 temperature) and (second near9 temperature) and molding and potting	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/19 08:23
S54	2593	((cure or curing) near9 resin) and ((bake or baking) near9 resin)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/19 08:24
S55	687	((cure or curing) near9 resin) and ((bake or baking) near9 resin) and (thermoset\$4 near resin)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/19 08:26
S56	622	((cure or curing) near9 resin) and ((bake or baking) near9 resin) and (thermoset\$4 near resin) and temperature	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/19 08:27

S57	2	((cure or curing) near9 resin) and ((bake or baking) near9 resin) and (thermoset\$4 near resin) and temperature and (inspect near9 (device or chip or IC))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/19 08:27
S58	2	((cure or curing) near9 resin) and ((bake or baking) near9 resin) and (thermoset\$4 near resin) and temperature and ((inspect or inspecting) near9 (device or chip or IC))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/19 08:51
S59	2	((cure or curing) near9 resin) and ((bake or baking) near9 resin) and (thermoset\$4 near resin) and temperature and package and inspect	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/19 08:51
S60	3	((cure or curing) near9 resin) and ((bake or baking) near9 resin) and temperature and package and inspect	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/19 08:53
S61	7235	package and (thermoset \$4 near resin)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/19 08:53
S62	2758	package and (thermoset \$4 near resin) and ((cure or curing) near9 resin)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/19 08:54
S63	68	package and (thermoset \$4 near resin) and ((cure or curing) near9 resin) and ((bake or baking) near9 resin)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/19 08:54
S64	60	package and (thermoset \$4 near resin) and ((cure or curing) near9 resin) and ((bake or baking) near9 resin) and temperature	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/19 08:54

S65	37	package and (thermoset \$4 near resin) and ((cure or curing) near9 resin) and ((bake or baking) near9 resin) and temperature and ((chip or IC or device or circuit) near9 resin)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/19 08:57
S66	14	package and (thermoset \$4 near resin) and ((cure or curing) near9 resin) and ((bake or baking) near9 resin) and temperature and ((chip or IC or device or circuit) near9 resin) and inspect\$4	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/19 08:57
S67	12	package and (thermoset \$4 near resin) and ((cure or curing) near9 resin) and ((bake or baking) near9 resin) and temperature and ((chip or IC or device or circuit) near9 resin) and ((inspect\$4 or monitor or test\$4) near9 (chip or IC or device or circuit))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/19 09:08
S68	149	((seal\$4 or encas\$4 or enclos\$4) near9 resin) and ((cure or curing) near9 resin) and ((bake or baking) near9 resin) and ((chip or ic or circuit or device or semiconductor) near9 resin)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/19 09:10
S69	149	((seal\$4 or encas\$4 or enclos\$4) near9 resin) and ((cure or curing) near9 resin) and ((bake or baking) near9 resin) and ((chip or IC or circuit or device or semiconductor) near9 resin)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/19 09:11

S70	143	((seal\$4 or encas\$4 or enclos\$4) near9 resin) and ((cure or curing) near9 resin) and ((bake or baking) near9 resin) and ((chip or IC or circuit or device or semiconductor) near9 resin) and temperature	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/19 09:11
S71	37	((seal\$4 or encas\$4 or enclos\$4) near9 resin) and ((cure or curing) near9 resin) and ((bake or baking) near9 resin) and ((chip or IC or circuit or device or semiconductor) near9 resin) and temperature and (thermoset\$4 near resin)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/19 09:11
S72	11	((seal\$4 or encas\$4 or enclos\$4) near9 resin) and ((cure or curing) near9 resin) and ((bake or baking) near9 resin) and ((chip or IC or circuit or device or semiconductor) near9 resin) and temperature and (thermoset\$4 near resin) and molding and potting	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/19 09:29
S73	1	((seal\$4 or encas\$4 or enclos\$4) near9 resin) and ((cure or curing) near9 resin) and ((bake or baking) near9 resin) and ((chip or IC or circuit or device or semiconductor) near9 resin) and temperature and (thermoset\$4 near resin) and molding and potting and (inspect or monitor or test)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/19 09:12
S74	399485	((seal\$4 or enclose\$4 or encas\$4) near9 (IC or chip or device or circuit or semiconductor))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/19 09:30

S75	54589	((seal\$4 or enclose\$4 or encas\$4) near9 (IC or chip or device or circuit or semiconductor)) same resin	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/19 09:31
S76	51	((seal\$4 or enclose\$4 or encas\$4) near9 (IC or chip or device or circuit or semiconductor)) same resin and ((curing or cure) near9 resin) and (bak\$4 near9 resin) and (thermoset\$4 near resin)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/19 09:32
S77	34	((seal\$4 or enclose\$4 or encas\$4) near9 (IC or chip or device or circuit or semiconductor)) same resin and ((curing or cure) near9 resin) and (bak\$4 near9 resin) and (thermoset\$4 near resin) and ((inspect\$4 or monitor\$4 or test\$4) same (IC or chip or device or circuit or semiconductor))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/19 09:46
S78	1899	(bak\$4 near9 thermoset \$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/12 14:11
S79	1070	(bak\$4 near9 thermoset \$4) near9 resin	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/12 14:11
S80	9	(bak\$4 near9 thermoset \$4) near9 resin and (third near9 temperature)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/12 14:12
S81	671	(bak\$4 near9 thermoset \$4) near9 resin and temperature	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/12 14:26

S82	13429	((bak\$4 or heat\$4) near9 thermoset\$4) near9 resin and temperature	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/12 14:27
S83	317	((bak\$4 or heat\$4) near9 thermoset\$4) near9 resin and (first near temperature)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/12 14:28
S84	160	((bak\$4 or heat\$4) near9 thermoset\$4) near9 resin and (first near temperature) and (second near temperature)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/12 14:28
S85	37	((bak\$4 or heat\$4) near9 thermoset\$4) near9 resin and (first near temperature) and (second near temperature) and (third near temperature)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/12 14:28
S86	24	((bak\$4 or heat\$4) near9 thermoset\$4) near9 resin and (first near temperature) and (second near temperature) and (third near temperature) and (cure or curing or cured)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/12 14:29
S87	2	"6331450".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2008/03/12 14:47
S88	20312	(bak\$4 or cook\$4) near9 resin	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/15 10:10
S89	25	(bak\$4 or cook\$4) near9 resin and (third near temperature)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/15 10:10

S90	2	(bak\$4 or cook\$4) near9 resin with (third near temperature)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/15 10:11
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